One Watt High Voltage Transistor

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-300	Vdc
Collector – Base Voltage	V _{CBO}	-300	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

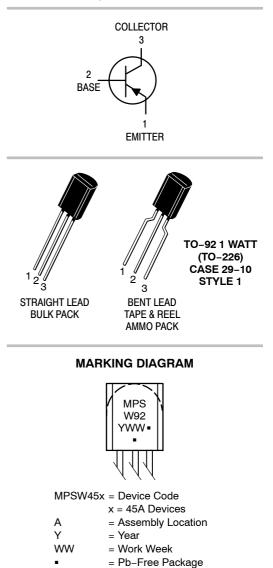
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	125	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com



ORDERING INFORMATION

(Note: Microdot may be in either location)

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MPSW92

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	
Collector – Emitter Breakdown Voltage (Note 1) ($I_C = -1.0$ mAdc, $I_B = 0$)	V _{(BR)CEO}	-300	_	Vdc
Collector-Base Breakdown Voltage ($I_C = -100 \ \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	-300	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -100 \ \mu Adc$, $I_C = 0$)	V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current ($V_{CB} = -200 \text{ Vdc}, I_E = 0$)	Ісво	-	-0.25	μAdc
Emitter Cutoff Current ($V_{EB} = -3.0$ Vdc, $I_C = 0$)	I _{EBO}	-	-0.1	μAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain ($I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}$) ($I_C = -10 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}$) ($I_C = -30 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}$)	h _{FE}	25 40 25	- - -	-
Collector-Emitter Saturation Voltage ($I_C = -20$ mAdc, $I_B = -2.0$ mAdc)	V _{CE(sat)}	-	-0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = -20$ mAdc, $I_B = -2.0$ mAdc)	V _{BE(sat)}	-	-0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product ($I_C = -10$ mAdc, $V_{CE} = -20$ Vdc, f = 20 MHz)	f _T	50	_	MHz
Collector-Base Capacitance $(V_{CB} = -20 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{cb}	-	6.0	pF

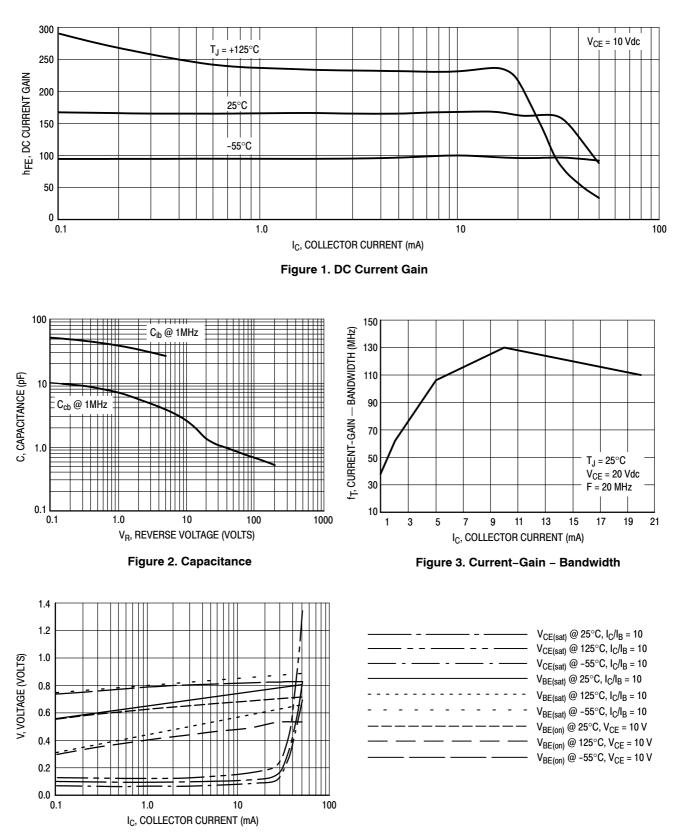
1. Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSW92	TO-92	5000 Units / Box
MPSW92G	TO-92 (Pb-Free)	5000 Units / Box
MPSW92RLREG	TO-92 (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

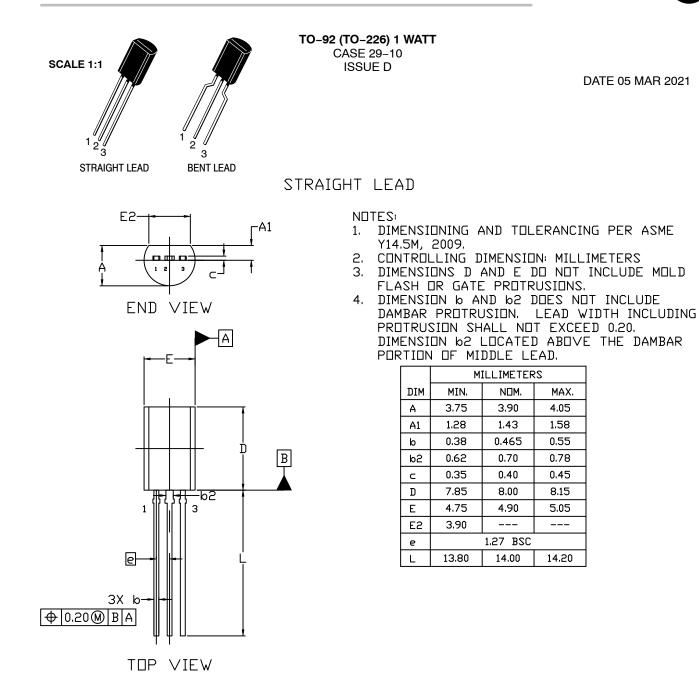
MPSW92





MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





STYLES AND MARKING ON PAGE 3

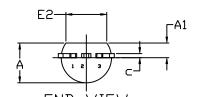
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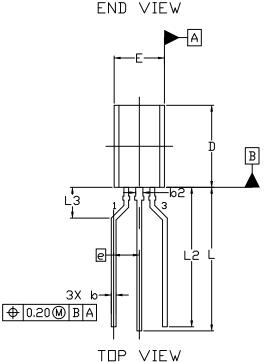


TO-92 (TO-226) 1 WATT CASE 29–10 ISSUE D

DATE 05 MAR 2021

FORMED LEAD





NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS,
- 4. DIMENSION ७ AND ७2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION ७2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
Α	3.75	3.90	4.05	
A1	1.28	1.43	1.58	
σ	0.38	0.465	0.55	
b2	0.62	0.70	0.78	
с	0.35	0.40	0.45	
D	7.85	8.00	8.15	
Е	4.75	4.90	5.05	
E2	3.90			
e	2.50 BSC			
L	13.80	14.00	14.20	
L2	13.20	13.60	14.00	
L3	3.00 REF			

STYLES AND MARKING ON PAGE 3

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DATE 05 MAR 2021

2.	EMITTER BASE COLLECTOR
STYLE 6: PIN 1. 2. 3.	SOURCE & SUBSTRATE
2.	ANODE CATHODE & ANODE CATHODE
2.	ANODE GATE CATHODE
2.	COLLECTOR EMITTER BASE
	V _{CC} GROUND 2 OUTPUT
	GATE DRAIN SOURCE

STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2 STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT STYLE 32 PIN 1. BASE 2. COLLECTOR 3. EMITTER

2	: ANODE ANODE CATHODE
2	: DRAIN GATE SOURCE & SUBSTRATE
2	3: ANODE 1 GATE CATHODE 2
2	8: ANODE CATHODE NOT CONNECTED
2	3: . Gate . Source . Drain
2	8: . CATHODE . ANODE . GATE
2	3: . Return . INPUT . Output

STYLE 4: PIN 1. CATHODE STYLE 5: 2. CATHODE 3. ANODE STYLE 9: PIN 1. BASE 1 EMITTER 2. 3. BASE 2 STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE STYLE 34: PIN 1. INPUT 2. GROUND

3. LOGIC

PIN 1. DRAIN 2. SOURCE 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

GENERIC MARKING DIAGRAM*

XXXXX XXXXX ALYW

XXXX = Specific Device Code

- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
 - = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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